MMBTA56W

Rev.E Mar.-2016

蓝箭电子
BLUE ROCKET ELECTRONICS

DATA SHEET

/ Descriptions

Silicon PNP transistor in a SOT-323 Plastic Package.

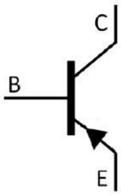
/ Features

Complements the MMBTA06W.

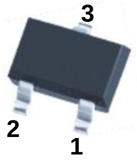
/ Applications

General purpose amplifier.

/ Equivalent Circuit



/ Pinning



PIN1 Emitter PIN 2 Base PIN 3 Collector

/ Marking

h_{FE} Range	>100
Marking	HR2G

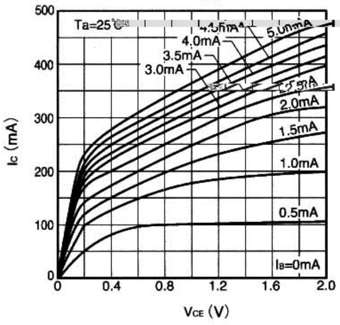
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-80	V
Collector to Emitter Voltage	V_{CEO}	-80	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-0.5	A
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55～150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-100μA I_E=0	-80			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-1.0mA I_B=0	-80			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-80 V I_E=0			-0.1	μA
Emitter Cut-Off Current	I_{CEO}	V_{CB}=-60 V I_B=0			-1.0	μA
Emitter Base Cut-Off Current	I_{EBO}	V_{BE}=-4.0V I_C=0			-0.1	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=-1.0V I_C=-100mA	100			
	$h_{FE(2)}$	V_{CE}=-1.0V I_C=-10mA	100			

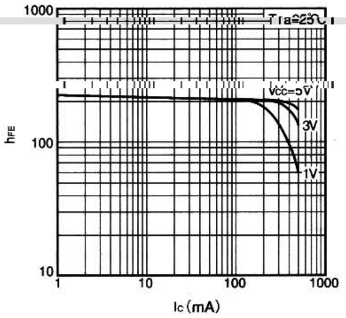
Collector to Emitter Saturation

/ Electrical Characteristic Curve

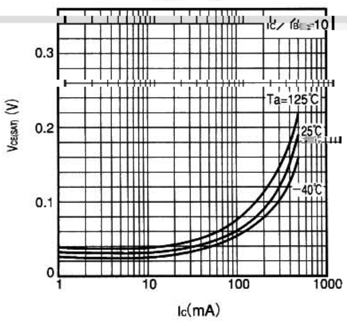
Ic — VCE



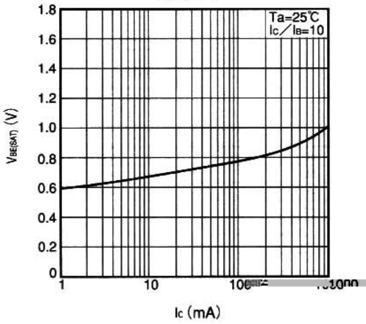
hFE — Ic



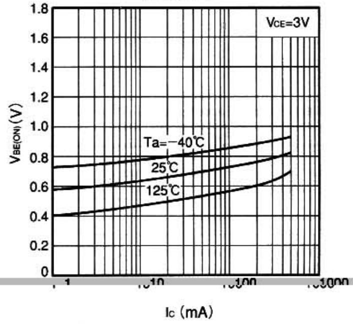
VCE(SAT) — Ic



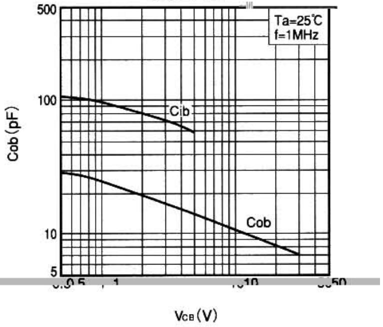
VBE(SAT) — Ic

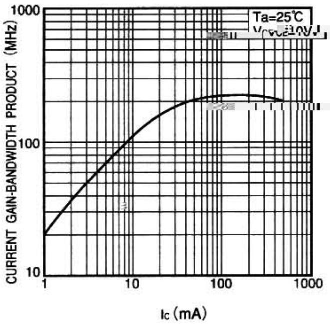


VBE(ON) — Ic

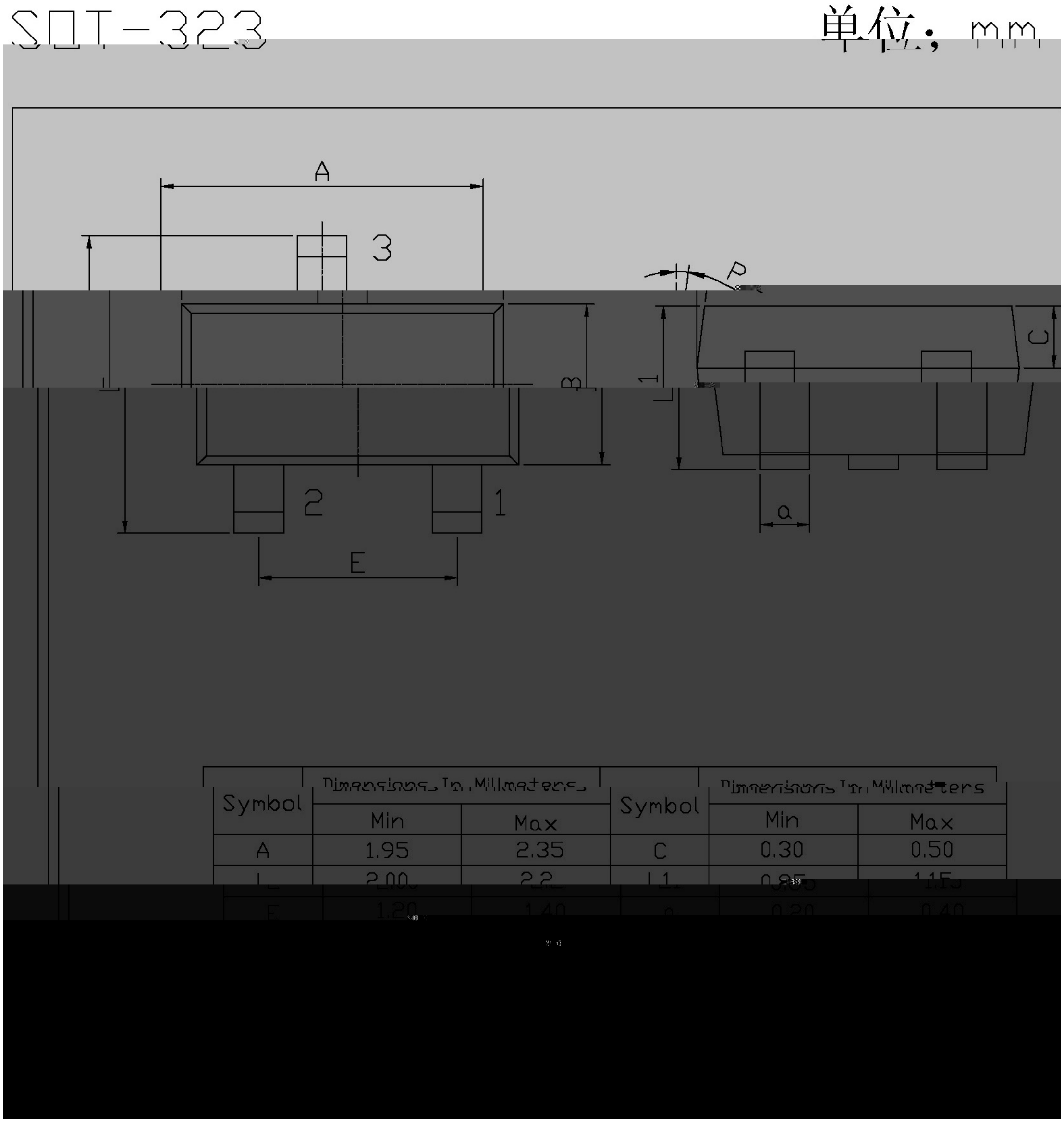


Cob — VCB



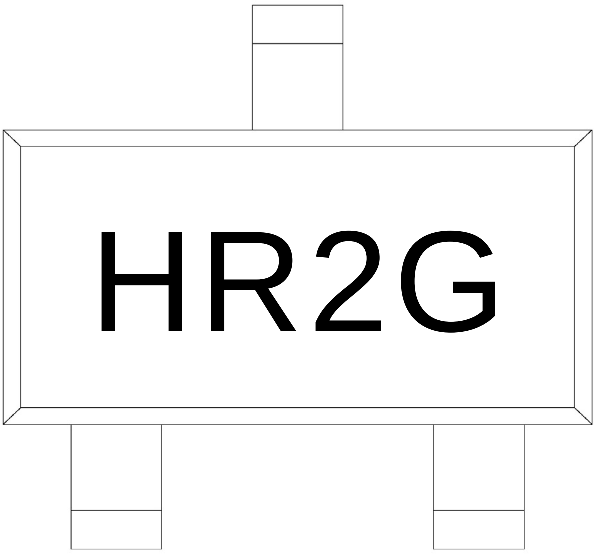


/ Package Dimensions



Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	1.95	2.35	C	0.30	0.50
L	2.00	2.2	L1	0.85	1.15
E	1.20	1.40	a	0.20	0.40

/ Marking Instructions



H

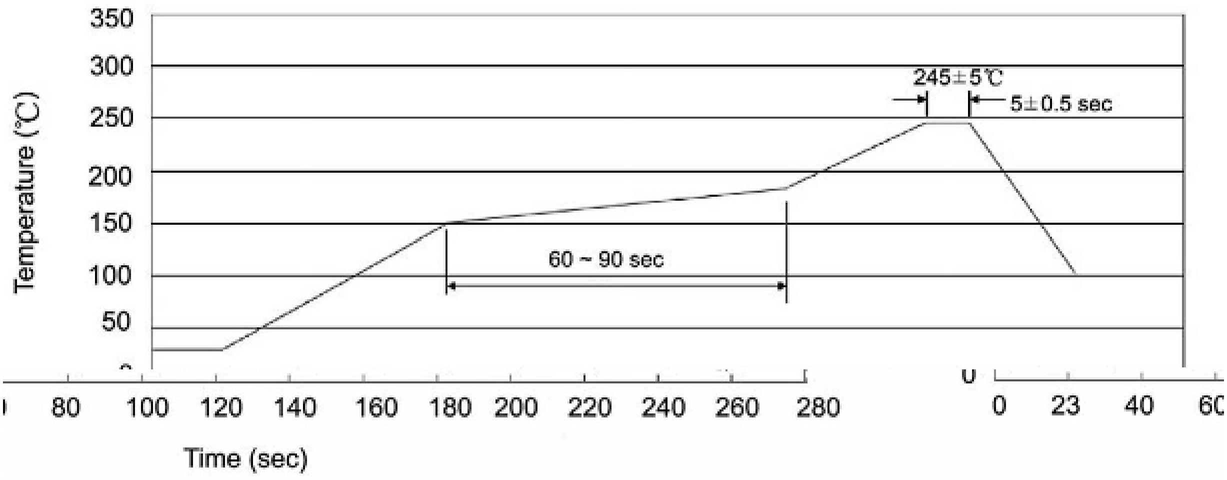
R2G

Note:

H: Company Code.

R2G: Product Type Code

( ) /



Note:

1 25 150 60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2 245 5 5 0.5sec;	2.Peak Temp.:245 5 , Duration:5 0.5sec.
3 2 10 /sec.	3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260 5 10 1 sec. Temp.:260 5 Time:10 1 sec

/ Packaging SPEC.

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm^3)		
	只 卷盘	卷盘 盒	只 盒	盒 箱	只 箱		盒	箱
						〃		